



Power-off Protection, 6 Ω , 1.8 V to 5.5 V, SPDT Analog Switch (2:1 Multiplexer)

DESCRIPTION

The DG2002E is a high performance single-pole, double-throw (SPDT) analog switch designed for 1.8 V to 5.5 V operation with a single power rail.

Fabricated with high density CMOS technology, the device achieves low on resistance of 6 Ω and switch off capacitance of 7 pF at a 5 V power supply and low power consumption, and fast switching speeds. Its charge injection is 1 pC.

The DG2002E can handle both analog and digital signals and permits signals with amplitudes of up to V+ to be transmitted in either direction. Its control logic inputs can go over V+ up to 5.5 V. It features break before make switching performance.

A powered-off protection circuit is built into the switch to prevent an abnormal current flow from COM pin to V+ during the power-down condition. Each output pin can withstand greater than 7 kV (human body model).

Operation temperature is specified from -40 °C to +85 °C. The DG2002E is available in the compact SC-70-6L package.

FEATURES

- Low switch on-resistance (6 Ω)
- +1.8 V to +5.5 V single supply operation
- Powered-off protection
- Control logic inputs can go over V+
- · Low parasitic capacitance, 7 pF at switch off
- Low charge injection, 1 pC
- · Break before make switching
- Latch-up performance exceeds 200 mA per JESD 78
- · High ESD rating
 - 7000 V human body model (JS-001)
- 1000 V charge device model (JS-002)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

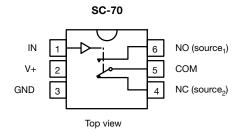
Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- · Battery powered devices
- Instrumentation
- Medical equipment
- Low voltage data acquisistion
- · Control and automation
- Consumer and computing

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device marking: H9

TRUTH TABLE						
LOGIC	NC	NO				
0	On	Off				
1	Of	On				

Pin 1 — H9XXX

Device marking: H9XXX XXX = Date / lot traceability code

ORDERING IN	RDERING INFORMATION					
TEMP. RANGE	ANGE PACKAGE PART NUMBE					
-40 °C to +85 °C	SC-70-6	DG2002EDL-T1-GE3				

Notes

- Logic "0" ≤ 0.8 V
- Logic "1" ≥ 2.4 V

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER		LIMIT	UNIT			
V+, COM, NC, NO, IN reference to GND		-0.3 to 6	V			
Continuous current (any terminal)		± 50	mA			
Peak current (pulsed at 1 ms, 10 % duty	cycle)	± 200	IIIA			
Storage temperature	Storage temperature		°C			
Power dissipation (packages) ^a	6-pin SC-70 ^b	250	mW			
ESD / HBM	JS-001	7000	V			
ESD / CDM	JS-002	1000	v			
Latch up	Per JESD78 with 1.5 x voltage clamp	200	mA			

- a. All leads welded or soldered to PC boardb. Derate 3.1 mW/°C above 70 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+	= 5 V)						
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.a	LIMITS -40 °C to +85 °C			UNIT
		V+ = 5 V, ± 10 % V _{IN} = 0.8 V or 2.4 V ^e		MIN. b	TYP. c	MAX. b	
Analog Switch	l		L			L	
Analog signal range ^d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0	-	V+	>
Drain-source on-resistance d	R _{DS(on)}	$V_{+} = 4.5 \text{ V}, V_{COM} = 3 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full	-	6 8	8 10	
R _{DS(on)} flatness ^d	R _{DS(on)} flatness	V+ = 5 V, V _{COM} = 1.5 V, 3.5 V, I _{NO} , I _{NC} = 10 mA	Room	-	0.4	-	Ω
R _{DS(on)} match ^d	$\Delta R_{DS(on)}$	$V+ = 4.5 \text{ V}, V_{COM} = 3 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$ Ro	Room	-	0.04	0.2	
	I _{NO(off)} ,		Room	-1.5	-	1.5	
Switch-off leakage current f	I _{NC(off)}	V+ = 5.5 V,	Full	-4	-	4	
Switch-off leakage current		V_{NO} , $V_{NC} = 1 \text{ V} / 4.5 \text{ V}$, $V_{COM} = 4.5 \text{ V} / 1 \text{ V}$	Room	-1	-	1	^
	I _{COM(off)}		Full	-4	-	4	nA
Observation test and a second f		V+ = 5.5 V,	Room	-1	-	1	
Channel-on leakage current f	I _{COM(on)}	V_{NO} , $V_{NC} = V_{COM} = 1 \text{ V} / 4.5 \text{ V}$	Full	-4	-	4	
Power-down leakage	I _{PD}	$V+=0$ V, $V_{COM}=5$ V, NO/NC open, $V_{IN}=GND$	Full	-	-	2	μA
		$V+=0$ V, V_{NO} , $V_{NC}=5$ V, COM open, $V_{IN}=GND$	Full	-	-	2	
Digital Control							
Input high voltage	V _{INH}		Full	2.4	-	-	V
Input low voltage	V_{INL}		Full	-	-	0.8	V
Input capacitance d	C _{IN}		Full	-	6	-	pF
Input current	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ V or V} +$	Full	-1	-	1	μΑ
Dynamic Characteristics							
Turn-on time d	+		Room	-	10	30	
rum-on ume -	t _{ON}		Full	-	-	32	
Turn-off time d		V_{NO} or $V_{NC} = 3 \text{ V}$, $R_{L} = 300 \Omega$, $C_{L} = 35 \text{ pF}$	Room	-	8	24	ns
rum-on time -	t _{OFF}		Full	-	-	26	
Break-before-make time ^d	t _{BBM}		Room	1	-	-	
Charge injection ^d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, V_{NO}, V_{NC} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room	-	1	-	рС
Off-isolation d	OIRR	D 5000 5 7 5 1 MHz	Room	-	-78	-	٩D
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	-	-77	-	dB
NO NC off conscitance d	C _{NO(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	7	-	
NO, NC off capacitance d	C _{NC(off)}		Room	-	7	-	pF
Channel-on capacitance d	C _{ON}		Room	-	13	-	1
Power Supply							
Power supply current ^d	l+	$V_{IN} = 0 \text{ V or V} +$	Full	-	0.004	1	μΑ



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PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.a	LIMITS -40 °C to +85 °C			UNIT
		$V+ = 3 V, \pm 10 \%$ $V_{IN} = 0.4 V \text{ or } 2 V^e$		MIN. b	TYP. c	MAX. b	
Analog Switch							
Analog signal range d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0	-	V+	V
Drain-source on-resistance d	R _{DS(on)}	$V+ = 2.7 \text{ V}, V_{COM} = 1.5 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full	-	13 15	22 24	
R _{DS(on)} flatness ^d	R _{DS(on)} flatness	$V+ = 3 V$, $V_{COM} = 0 V$ to $V+$, I_{NO} , $I_{NC} = 10 \text{ mA}$	Room	-	1.4	-	Ω
R _{DS(on)} match ^d	$\Delta R_{DS(on)}$	V+ = 2.7 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 10 mA	Room	-	0.03	0.35	
	I _{NO(off)} ,		Room	-0.4	-	0.4	
Cwitch off looks as surrent f	I _{NC(off)}	V+ = 3.3 V,	Full	-4	-	4	nA
Switch-off leakage current f	-	V_{NO} , $V_{NC} = 1 \text{ V} / 3 \text{ V}$, $V_{COM} = 3 \text{ V} / 1 \text{ V}$	Room	-0.8	-	0.8	
	I _{COM(off)}		Full	-8	-	8	
		V+ = 3.3 V,	Room	-0.8	-	0.8	nA
Channel-on leakage current f	I _{COM(on)}	V_{NO} , $V_{NC} = V_{COM} = 1 \text{ V} / 3 \text{ V}$	Full	-8	-	8	
Digital Control							
Input high voltage	V_{INH}		Full	2	-	-	V
Input low voltage	V_{INL}		Full	ı	-	0.4	V
Input capacitance d	C _{IN}		Full	ı	6	-	рF
Input current	I _{INL} or I _{INH}	$V_{IN} = 0 V \text{ or } V+$	Full	-1	-	1	μΑ
Dynamic Characteristics							
Turn-on time d	+		Room	ı	13	34	
rum-on ume -	t _{ON}		Full	ı	-	37	
Turn-off time d		V_{NO} or V_{NC} = 2 V, R_L = 300 Ω , C_L = 35 pF	Room	-	9	20	ns
rum-on time s	t _{OFF}		Full	-	-	22	
Break-before-make time d	t _{BBM}		Room	1	-	-	
Charge injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, V_{NO} , V_{NC} = 0 V, R_{GEN} = 0 Ω	Room	-	0.9	-	рС
Off-isolation d	OIRR	D 5000 C 5 7 5 1 MH-	Room	-	-78	-	٩D
Crosstalk ^d	X _{TALK}	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz	Room	-	-77	-	dB
NO NO off conscitance d	C _{NO(off)}		Room	-	7	-	
NO, NC off capacitance d	$V_{IN} = 0 \text{ V or V+, f} = 1 \text{ MHz}$	$V_{IN} = 0 V \text{ or } V+, f = 1 MHz$	Room	-	7	-	рF
Channel-on capacitance d	C _{ON}	¬	Room	-	14	-	1
Power Supply					•		



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PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. a	LIMITS -40 °C to +85 °C			UNIT
		$V+ = 2.5 V, \pm 10 \%$ $V_{IN} = 0.4 V \text{ or } 2 V^e$		MIN. b	TYP. c	MAX. b	0
Analog Switch							
Analog signal range ^d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0	-	V+	V
Drain-source on-resistance d	R _{DS(on)}	$V+ = 2.2 \text{ V}, V_{COM} = 1 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full ^d	-	23 24	27 28	
R _{DS(on)} flatness ^d	R _{DS(on)} flatness	V+ = 2.5 V, V _{COM} = 0 V to V+, I _{NO} , I _{NC} = 10 mA	Room	-	1.7	-	Ω
R _{DS(on)} match ^d	$\Delta R_{DS(on)}$	V+ = 2.2 V, V _{COM} = 1.2 V, I _{NO} , I _{NC} = 10 mA	Room	-	0.1	0.5	
	I _{NO(off)} ,		Room	-0.2	-	0.2	
Owitals afficiency assument f	I _{NC(off)}	V+ = 2.7 V,	Full ^d	-3	-	3	nA
Switch-off leakage current f		V_{NO} , $V_{NC} = 0.5 \text{ V} / 1.5 \text{ V}$, $V_{COM} = 1.5 \text{ V} / 0.5 \text{ V}$	Room	-0.2	-	0.2	
	I _{COM(off)}	Full d	-3	-	3	†	
Channel-on leakage current f		V+ = 2.7 V,	Room	-0.2	-	0.2	nA
	I _{COM(on)}	V_{NO} , $V_{NC} = V_{COM} = 0.5 \text{ V} / 1.5 \text{ V}$	Full ^d	-3	-	3	
Digital Control							
Input high voltage	V _{INH}		Full	2	-	-	V
Input low voltage	V_{INL}		Full	-	-	0.4	ľ
Input capacitance d	C _{IN}		Full	-	6	-	pF
Input current	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ V or V} +$	Full	-1	-	1	μΑ
Dynamic Characteristics							
Turn-on time d	+		Room	-	16	36	
rum-on time -	t _{ON}		Full ^d	-	-	38	
Turn-off time d		V_{NO} or $V_{NC} = 1.5 \text{ V}$, $R_{L} = 300 \Omega$, $C_{L} = 35 \text{ pF}$	Room	-	10	19	ns
rum-on time s	t _{OFF}		Full	-	-	21	
Break-before-make time ^d	t _{BBM}		Room d	1	-	-	
Charge injection ^d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, V_{NO}, V_{NC} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room	-	0.9	-	рС
Off-isolation ^d	OIRR	D 5000 5 F 5 1 MH-	Room	-	-78	-	-10
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	-	-77	-	dB
NO NO off conscitons - d	C _{NO(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	7	-	pF
NO, NC off capacitance d	C _{NC(off)}		Room	-	7	-	
Channel-on capacitance d	C _{ON}		Room	-	14	-	ĺ
Power Supply							
Power supply current ^d	I+	$V_{IN} = 0 \text{ V or V} +$	Full	_	_	1	μΑ



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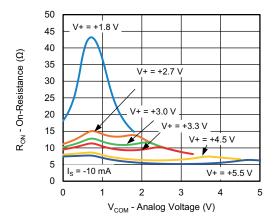
SPECIFICATIONS (V+	= 2 V)						
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.a	LIMITS -40 °C to +85 °C			UNIT
		V+ = 2 V, ± 10 % V _{IN} = 0.4 V or 1.6 V ^e	I LIVIF.	MIN. b	TYP. c	MAX. b	UNIT
Analog Switch							,
Analog signal range ^d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0	-	V+	V
Drain-source on-resistance d	R _{DS(on)}	V+ = 1.8 V, V _{COM} = 1 V, I _{NO} , I _{NC} = 10 mA	Room Full ^d	-	37 36	42 44	
R _{DS(on)} flatness ^d	R _{DS(on)} flatness	V+ = 2 V, V _{COM} = 0 V to V+, I _{NO} , I _{NC} = 10 mA	Room	-	3	-	Ω
R _{DS(on)} match ^d	$\Delta R_{DS(on)}$	V+ = 1.8 V, V _{COM} = 1 V, I _{NO} , I _{NC} = 10 mA	Room	-	0.04	0.5	
	I _{NO(off)} ,		Room	-0.2	-	0.2	
Outtale off lands as assumed f	I _{NC(off)}	V+ = 2.2 V,	Full ^d	-3	-	3	nA
Switch-off leakage current f		V_{NO} , $V_{NC} = 0.5 \text{ V} / 1.5 \text{ V}$, $V_{COM} = 1.5 \text{ V} / 0.5 \text{ V}$	Room	-0.2	-	0.2	
	I _{COM(off)}		Full ^d	-3	-	3	
Observation to the first of the	I _{COM(on)}	$V_{+} = 2.2 \text{ V},$ $V_{NO}, V_{NC} = V_{COM} = 0.5 \text{ V} / 1.5 \text{ V}$	Room	-0.2	-	0.2	A
Channel-on leakage current f			Full ^d	-3	-	3	nA
Digital Control							
Input high voltage	V_{INH}		Full	1.6	-	-	V
Input low voltage	V_{INL}		Full	-	-	0.4	V
Input capacitance d	C _{IN}		Full	-	6	-	pF
Input current	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ V or V} +$	Full	-1	-	1	μΑ
Dynamic Characteristics							
Turn-on time d	tou		Room	-	21	40	
rum-on time	t _{ON}		Full ^d	-	-	42	
Turn-off time d	t	V_{NO} or V_{NC} = 1.5 V, R_L = 300 Ω , C_L = 35 pF	Room	-	13	20	ns
rum-on time	t _{OFF}		Full ^d	-	-	21	
Break-before-make time ^d	t _{BBM}		Room	1	-	-	
Charge injection ^d	Q_{INJ}	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, V_{NO}, V_{NC} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room	-	8.0	-	рС
Off-isolation ^d	OIRR	P 50 O. C 5 pE f _ 1 MHz	Room	-	-78	-	dB
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	-	-77	-	ub
NO, NC off capacitance d	C _{NO(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	7	-	
NO, NO OII Capacitance	C _{NC(off)}		Room	-	7	-	рF
Channel-on capacitance d	C _{ON}		Room	-	14	-	
Power Supply							
Power supply current ^d	I+	$V_{IN} = 0 \text{ V or V} +$	Full	-	-	1	μΑ

Notes

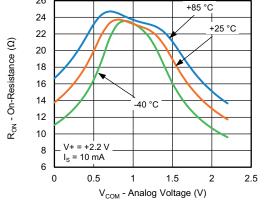
- a. Room = 25 °C, full = as determined by the operating suffix
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- c. Typical values are for design aid only, not guaranteed nor subject to production testing
- d. Guarantee by design, nor subjected to production test
- e. V_{IN} = input voltage to perform proper function
- f. Guaranteed by 5 V leakage testing, not production tested



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

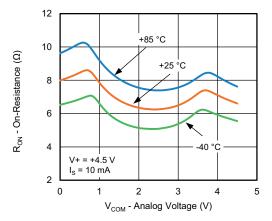


R_{DS(on)} vs. V_{COM} and Supply Voltage

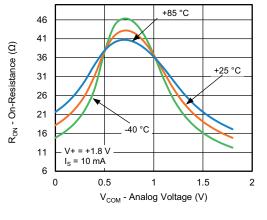


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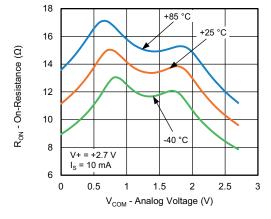
R_{DS(on)} vs. Analog Voltage and Temperature



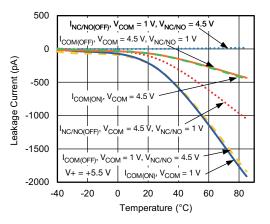
R_{DS(on)} vs. Analog Voltage and Temperature



R_{DS(on)} vs. Analog Voltage and Temperature



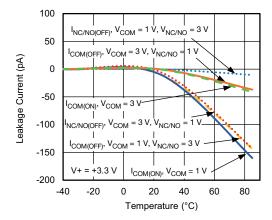
R_{DS(on)} vs. Analog Voltage and Temperature



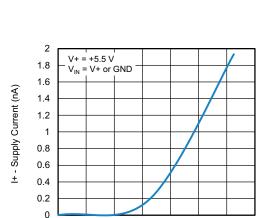
Leakage Current vs. Temperature



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Leakage Current vs. Temperature



Supply Current vs. Temperature

Temperature (°C)

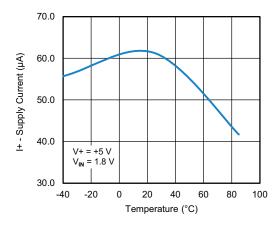
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20

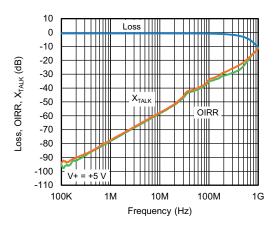
60

80

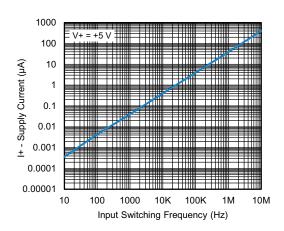
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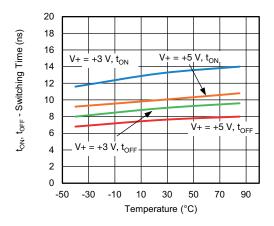
Supply Current vs. Temperature



Insertion Loss, Off-Isolation Crosstalk vs. Frequency



Supply Current vs. Input Switching Frequency



Switching Time vs. Temperature

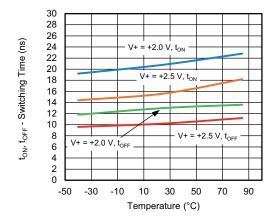
-40

-20

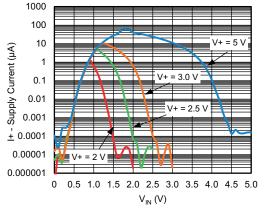
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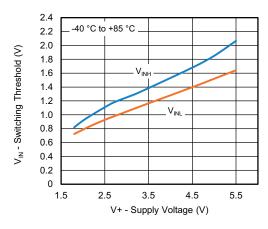
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



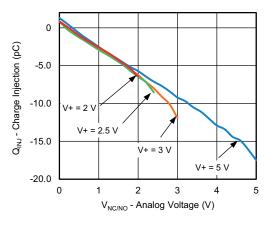
Switching Time vs. Temperature



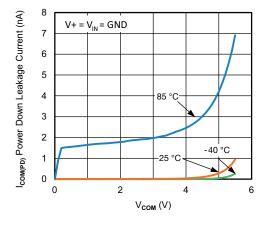
Supply Current vs. Enable Input Voltage



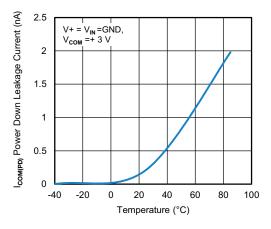
Switching Threshold vs. Supply Voltage



Charge Injection vs. Analog Voltage



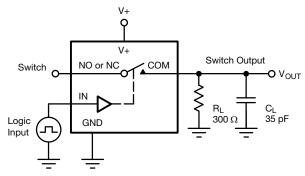
Power Down Leakage Current vs V_{COM}



Power Down Leakage Current vs Temperature

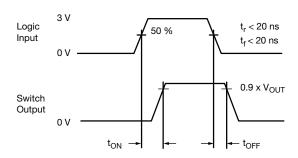


TEST CIRCUITS



C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = switch on

Logic input waveforms inverted for switches that have the opposite logic sense.

Fig. 1 - Switching Time

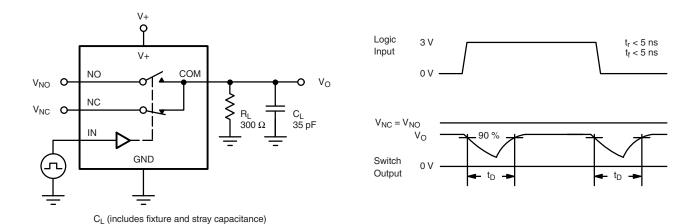


Fig. 2 - Break-Before-Make Interval

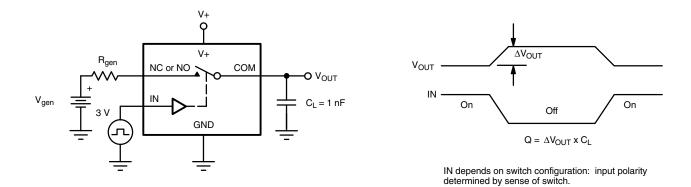


Fig. 3 - Charge Injection

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TEST CIRCUITS

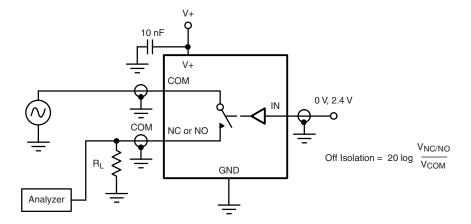


Fig. 4 - Off-Isolation

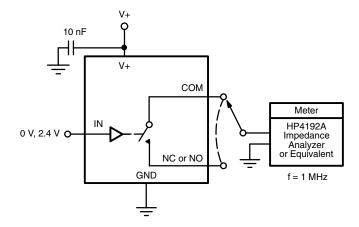


Fig. 5 - Channel Off / On Capacitance

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